

Benjamin Olson

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

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|-------------------|-----------------------|----------------|-----------------|
| 15 papers | 439 citations | 11 h-index | 16 g-index |
| 16 ext. papers | 499 ext. citations | 3.1 avg, IF | 2.82 L-index |

| # | Paper | IF | Citations |
|----|---|-----|-----------|
| 15 | Effects of electron doping level on minority carrier lifetimes in n-type mid-wave infrared InAs/InAs _{1-x} Sb _x type-II superlattices. <i>Applied Physics Letters</i> , 2016 , 109, 261105 | 3.4 | 17 |
| 14 | Optical and electrical properties of narrow-bandgap infrared W-structure superlattices incorporating AlAs/AlSb/AlAs barrier layers. <i>Applied Physics Letters</i> , 2016 , 108, 252104 | 3.4 | 6 |
| 13 | Bandgap and temperature dependence of Auger recombination in InAs/InAsSb type-II superlattices. <i>Journal of Applied Physics</i> , 2016 , 119, 215705 | 2.5 | 20 |
| 12 | Contactless measurement of equilibrium electron concentrations in n-type InAs/InAs _{1-x} Sb _x type-II superlattices. <i>Applied Physics Letters</i> , 2016 , 109, 022105 | 3.4 | 1 |
| 11 | Far infrared edge photoresponse and persistent edge transport in an inverted InAs/GaSb heterostructure. <i>Applied Physics Letters</i> , 2016 , 108, 013106 | 3.4 | 8 |
| 10 | Enhanced infrared detectors using resonant structures combined with thin type-II superlattice absorbers. <i>Applied Physics Letters</i> , 2016 , 109, 251103 | 3.4 | 21 |
| 9 | Temperature-dependent optical measurements of the dominant recombination mechanisms in InAs/InAsSb type-II superlattices. <i>Journal of Applied Physics</i> , 2015 , 118, 125701 | 2.5 | 19 |
| 8 | Minority carrier lifetime and dark current measurements in mid-wavelength infrared InAs _{0.91} Sb _{0.09} alloy nBn photodetectors. <i>Applied Physics Letters</i> , 2015 , 107, 183504 | 3.4 | 18 |
| 7 | Auger recombination in long-wave infrared InAs/InAsSb type-II superlattices. <i>Applied Physics Letters</i> , 2015 , 107, 261104 | 3.4 | 21 |
| 6 | Demonstration of long minority carrier lifetimes in very narrow bandgap ternary InAs/GaInSb superlattices. <i>Applied Physics Letters</i> , 2015 , 107, 131102 | 3.4 | 6 |
| 5 | Effects of layer thickness and alloy composition on carrier lifetimes in mid-wave infrared InAs/InAsSb superlattices. <i>Applied Physics Letters</i> , 2014 , 105, 022107 | 3.4 | 52 |
| 4 | Identification of dominant recombination mechanisms in narrow-bandgap InAs/InAsSb type-II superlattices and InAsSb alloys. <i>Applied Physics Letters</i> , 2013 , 103, 052106 | 3.4 | 59 |
| 3 | All-optical measurement of vertical charge carrier transport in mid-wave infrared InAs/GaSb type-II superlattices. <i>Applied Physics Letters</i> , 2013 , 102, 202101 | 3.4 | 23 |
| 2 | Time-resolved optical measurements of minority carrier recombination in a mid-wave infrared InAsSb alloy and InAs/InAsSb superlattice. <i>Applied Physics Letters</i> , 2012 , 101, 092109 | 3.4 | 154 |
| 1 | Post growth annealing study on long wavelength infrared InAs/GaSb superlattices. <i>Journal of Applied Physics</i> , 2012 , 111, 053113 | 2.5 | 14 |